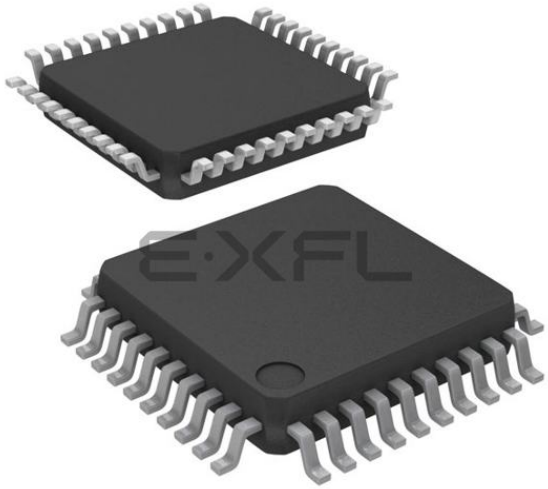
Renesas Electronics America Inc - R5F11EB8AFP#30 Datasheet



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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	25
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 8x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f11eb8afp-30

○ ROM, RAM capacities

Flash ROM	RAM	30 pins	32 pins	44 pins
16 KB	1.5 KB Note	R5F11EAAASP	R5F11EBAAFP	R5F11EFAAFP
8 KB		R5F11EA8ASP	R5F11EB8AFP	R5F11EF8AFP

Note This is 630 bytes when the self-programming function is used.

1.2 List of Part Numbers

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1G

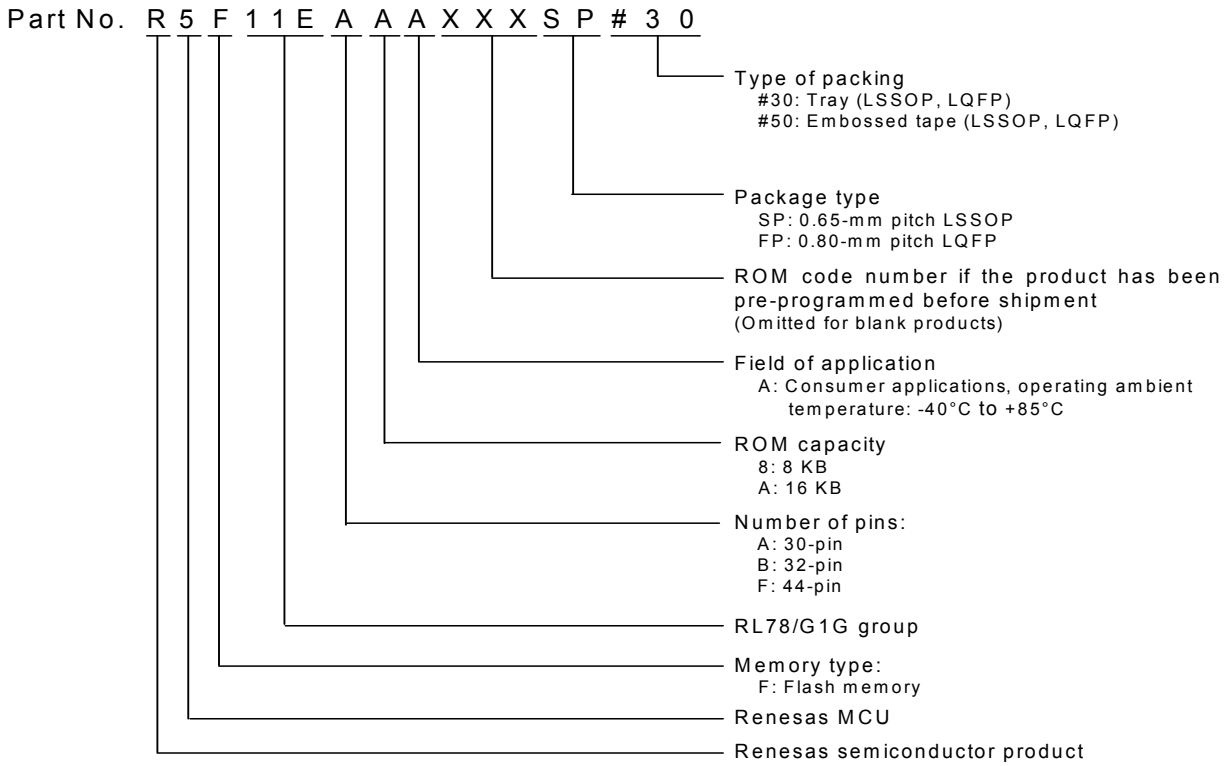
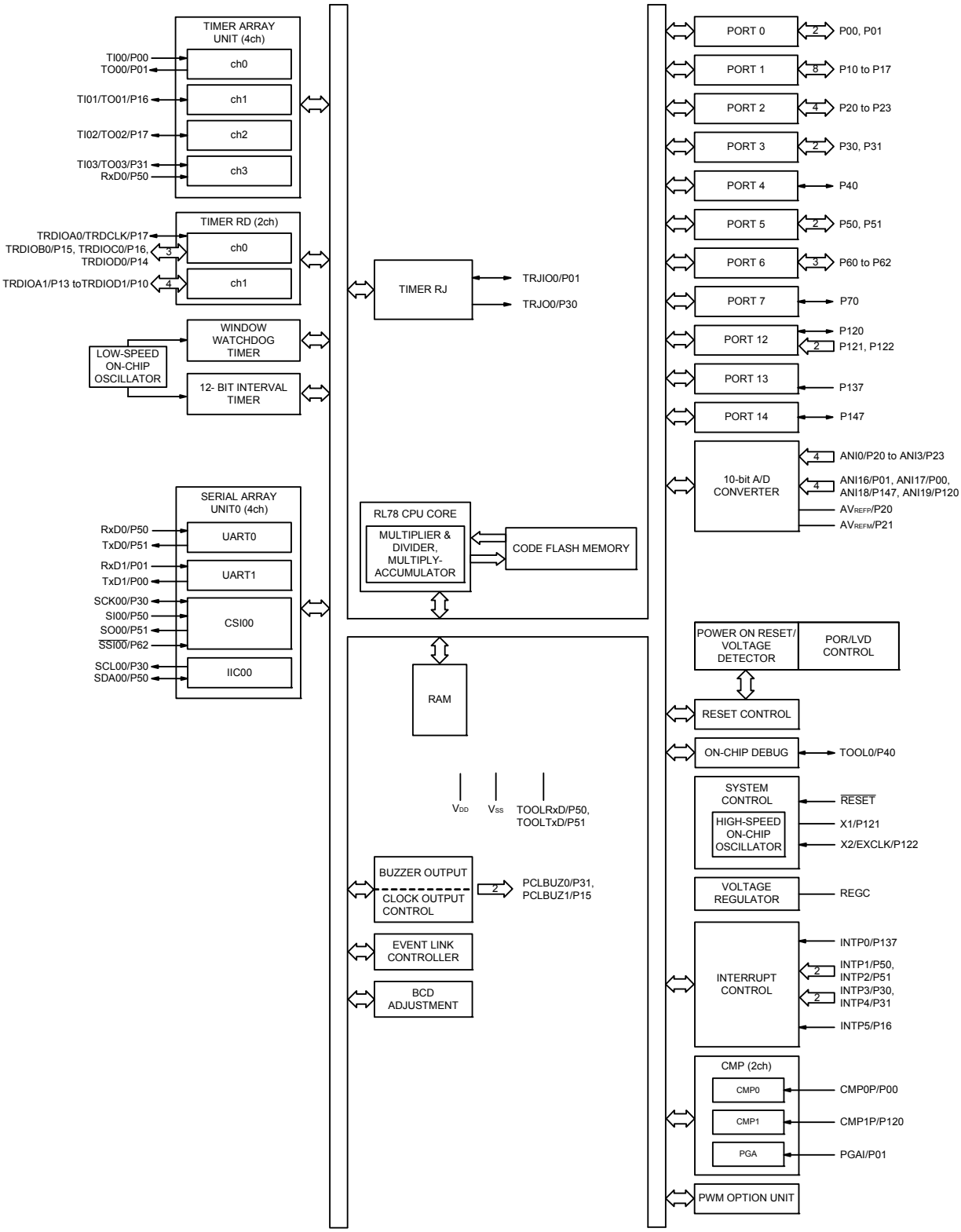


Table 1 - 1 Orderable Part Numbers

Pin Count	Package	Part Number
44 pins	44-pin plastic LQFP (10 × 10 mm)	R5F11EFAAFP#30, R5F11EFAAFP#50
		R5F11EF8AFP#30, R5F11EF8AFP#50
32 pins	32-pin plastic LQFP (7 × 7 mm)	R5F11EBAAFP#30, R5F11EBAAFP#50
		R5F11EB8AFP#30, R5F11EB8AFP#50
30 pins	30-pin plastic LSSOP (7.62 mm (300))	R5F11EAAASP#30, R5F11EAAASP#50
		R5F11EA8ASP#30, R5F11EA8ASP#50

1.5.2 32-pin products



1.6 Outline of Functions

[30-pin, 32-pin, 44-pin products (code flash memory 8 KB to 16 KB)]

Caution The above outline of the functions applies when peripheral I/O redirection register 1 (PIOR1) is set to 00H.

(1/2)

Item		30-pin	32-pin	44-pin
		R5F11EA8ASP, R5F11EAAASP	R5F11EB8AFP, R5F11EBAAFP	R5F11EF8AFP, R5F11EFAAFP
Code flash memory (KB)		8 to 16		
RAM (KB)		1.5		
Address space		1 MB		
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V)		
	High-speed on-chip oscillator clock (f_{IH})	LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 2.7 to 5.5 V) HS (high-speed main) mode: 1 to 24 MHz (V_{DD} = 2.7 to 5.5 V)		
Low-speed on-chip oscillator clock		15 kHz (TYP.): V_{DD} = 2.7 to 5.5 V		
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)		
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator clock: f_{IH} = 24 MHz operation)		
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)		
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.		
I/O port	Total	26	28	40
	CMOS I/O	23	25	35
	CMOS input	3	3	5
	CMOS output	—		
	N-ch open-drain I/O (6 V tolerance)	—		
Timer	16-bit timer	7 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels)		
	Watchdog timer	1 channel		
	12-bit interval timer	1 channel		
	Timer output	Timer outputs: 14 channels PWM outputs: 9 channels		

Caution Since a library is used when rewriting the flash memory using the user program, flash ROM and RAM areas are used. Refer to the RL78 Family Flash Self-Programming Library Type01 User's Manual before using these products.

2.3 Oscillator Characteristics

2.3.1 X1 oscillator characteristics

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X) Note	Ceramic resonator/ crystal resonator	2.7 V ≤ V_{DD} ≤ 5.5 V	1.0		20.0	MHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution **Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.**

Remark When using the X1 oscillator, refer to **5.4 System Clock Oscillator in the RL78/G1G User's Manual.**

2.3.2 On-chip oscillator characteristics

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f_{IH}		1		24	MHz
	f_{HOCO}		1		48	
High-speed on-chip oscillator clock frequency accuracy			-2		+2	%
Low-speed on-chip oscillator clock frequency	f_{IL}			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to **AC Characteristics** for instruction execution time.

2.4 DC Characteristics

2.4.1 Pin characteristics

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	2.7 V ≤ V_{DD} ≤ 5.5 V			-10.0 Note 2	mA
		Total of P00, P01, P40, P41, P120 (When duty ≤ 70% Note 3)	4.0 V ≤ V_{DD} ≤ 5.5 V			-55.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			-10.0	mA
		Total of P10 to P17, P30, P31, P50, P51, P60 to P63, P70 to P73, P146, P147 (When duty ≤ 70% Note 3)	4.0 V ≤ V_{DD} ≤ 5.5 V			-80.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			-19.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 5.5 V			-135.0	mA
	I_{OH2}	Per pin for P20 to P27	2.7 V ≤ V_{DD} ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 5.5 V			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≈ -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.
A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P10, P15, P17, P30, P50, P51 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120 to P124, P146, P147	Normal input buffer	0.8 V_{DD}		V_{DD}	V
	V_{IH2}	P01, P10, P15 to P17, P30, P31, P50	TTL input buffer 4.0 V ≤ V_{DD} ≤ 5.5 V	2.2		V_{DD}	V
			TTL input buffer 3.3 V ≤ V_{DD} < 4.0 V	2.0		V_{DD}	V
			TTL input buffer 2.7 V ≤ V_{DD} < 3.3 V	1.50		V_{DD}	V
	V_{IH3}	P20 to P27		0.7 V_{DD}		V_{DD}	V
	V_{IH4}	EXCLK, $\overline{\text{RESET}}$		0.8 V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120 to P124, P146, P147	Normal input buffer	0		0.2 V_{DD}	V
	V_{IL2}	P01, P10, P15 to P17, P30, P31, P50	TTL input buffer 4.0 V ≤ V_{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ V_{DD} < 4.0 V	0		0.5	V
			TTL input buffer 2.7 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P20 to P27		0		0.3 V_{DD}	V
	V_{IL4}	EXCLK, $\overline{\text{RESET}}$		0		0.2 V_{DD}	V

Caution The maximum value of V_{IH} of pins P00, P10, P15, P17, P30, P50, and P51 is V_{DD}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = -10.0 mA	V_{DD} - 1.5			V
			4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = -3.0 mA	V_{DD} - 0.7			V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = -2.0 mA	V_{DD} - 0.6			V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = -1.0 mA	V_{DD} - 0.5			V
	V_{OH2}	P20 to P27	2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = -100 μA	V_{DD} - 0.5			V
Output voltage, low	V_{OL1}	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 20.0 mA			1.3	V
			4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 0.3 mA			0.4	V
	V_{OL2}	P20 to P27	2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400 μA			0.4	V

Caution P00, P10, P15, P17, P30, P50, and P51 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00, P01, P10 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P123, P124, P137, P146, P147, $\overline{\text{RESET}}$	$V_I = V_{DD}$				1	μA
	I_{LIH2}	P121, P122 (X1, X2, EXCLK)	$V_I = V_{DD}$	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	I_{LIL1}	P00, P01, P10 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P123, P124, P137, P146, P147, $\overline{\text{RESET}}$	$V_I = V_{SS}$				-1	μA
	I_{LIL2}	P121, P122 (X1, X2, EXCLK)	$V_I = V_{SS}$	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	R_U	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	$V_I = V_{SS}$, in input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.5 AC Characteristics

2.5.1 Basic operation

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
			LS (low-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
			LS (low-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
TI00 to TI03 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns
Timer RJ input cycle	f_C	TRJIO		2.7 V ≤ V_{DD} ≤ 5.5 V	100			ns
Timer RJ input high-level width, low-level width	f_{WH}, f_{WL}	TRJIO		2.7 V ≤ V_{DD} ≤ 5.5 V	40			ns
TO00 to TO03, TRJIO0,TRJO, TRDIOA0/1, TRDIOB0/1, TRDIOC0/1,TRDIOD0/1 output frequency	f_{TO}	HS (high-speed main) mode		4.0 V ≤ V_{DD} ≤ 5.5 V			12	MHz
				2.7 V ≤ V_{DD} < 4.0 V			8	MHz
		LS (low-speed main) mode		2.7 V ≤ V_{DD} ≤ 5.5 V			4	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode		4.0 V ≤ V_{DD} ≤ 5.5 V			16	MHz
				2.7 V ≤ V_{DD} < 4.0 V			8	MHz
		LS (low-speed main) mode		2.7 V ≤ V_{DD} ≤ 5.5 V			4	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0 to INTP5		2.7 V ≤ V_{DD} ≤ 5.5 V	1			μs
Key interrupt input low-level width	t_{KR}	KR0-KR3		2.7 V ≤ V_{DD} ≤ 5.5 V	250			ns
$\overline{\text{RESET}}$ low-level width	t_{RSL}				10			μs

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))

(5) During communication at same potential (simplified I²C mode)

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		400 Note 1	kHz
		2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ		400 Note 1		400 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		ns
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 85 Note 2		1/f_{MCK} + 145 Note 2		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 145 Note 2		1/f_{MCK} + 145 Note 2		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	ns
		2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	0	355	0	355	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

Note 2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

(Remaks are listed on the next page.)

(8) Communication at different potential (2.5 V, 3 V) (f_{MCK}/4) (CSI mode) (master mode, SCKp... internal clock output)
(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)(1/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	300		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500		1150		ns
			2.7 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 75		t_{KCY1}/2 - 75		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		ns
		2.7 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 12		t_{KCY1}/2 - 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 18		t_{KCY1}/2 - 50		ns
		2.7 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns

Caution 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Caution 2. Use it with $V_{DD} \geq V_b$.

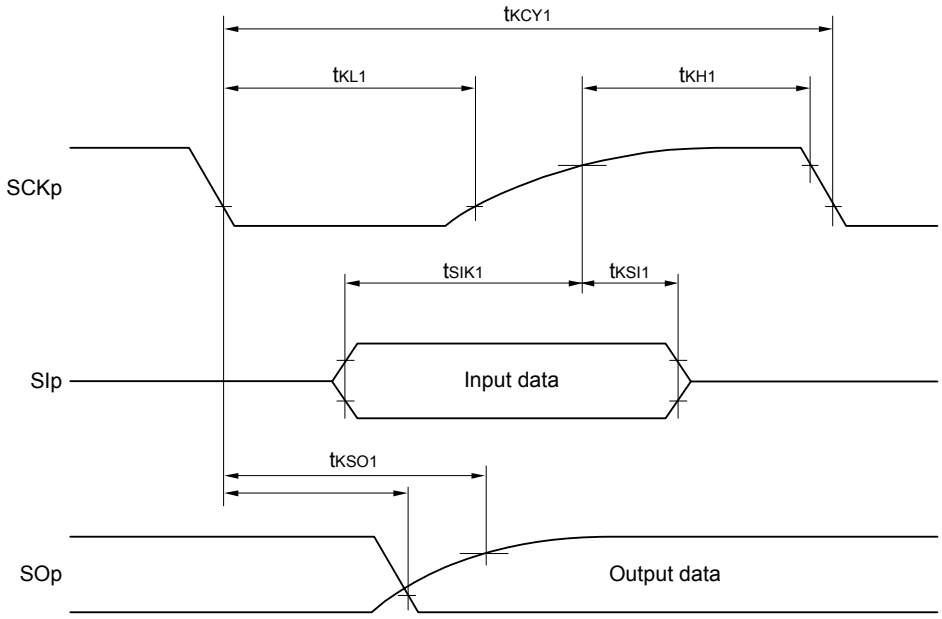
Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)

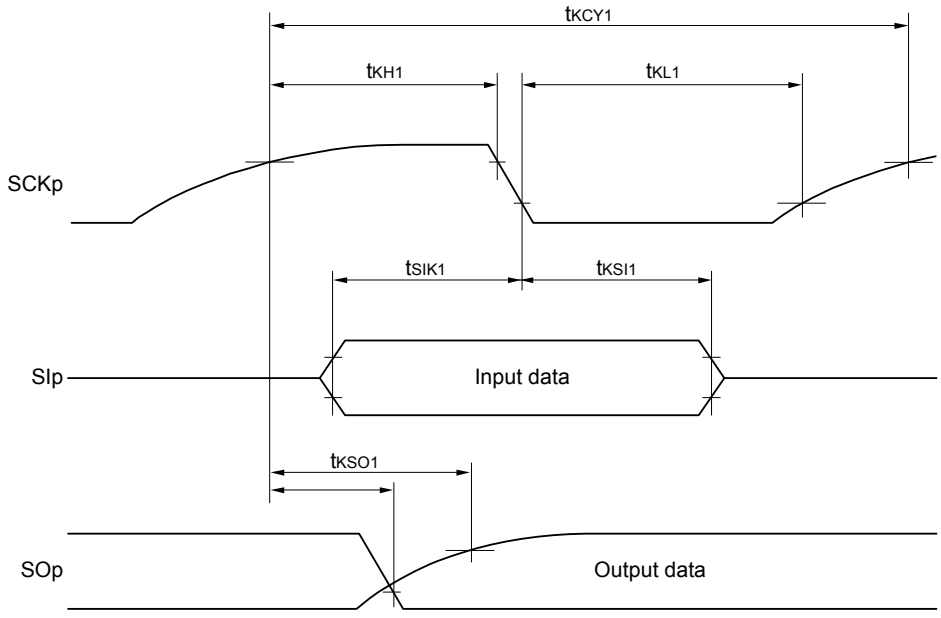
Remark 3. V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V: V_{IH} = 2.2 V, V_{IL} = 0.8 V
2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V: V_{IH} = 2.0 V, V_{IL} = 0.5 V

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)

(4) When AVREF (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), AVREF (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI0 to ANI7, ANI16 to ANI19

(TA = -40 to +85°C, 2.7 V ≤ VDD ≤ 5.5 V, VSS = 0 V, Reference voltage (+) = VBGR, Reference voltage (-) = AVREFM = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tCONV	8-bit resolution	2.7 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	EZS	8-bit resolution	2.7 V ≤ VDD ≤ 5.5 V			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	2.7 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.7 V ≤ VDD ≤ 5.5 V			±1.0	LSB
Reference voltage (+)	VBGR			1.38	1.45	1.5	V
Analog input voltage	VAIN			0		VBGR	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

2.7.2 Temperature sensor characteristics

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Reference output voltage	V_{CONST}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	t_{AMP}		5			μs

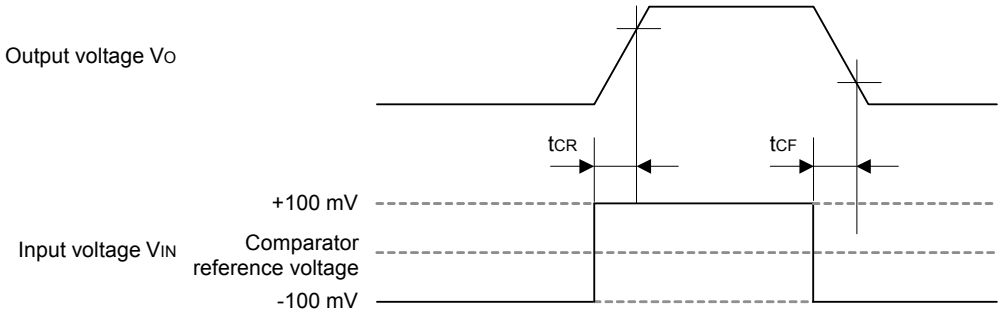
2.7.3 Comparator

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	V_{IOCMP}				±5	±40	mV
Input voltage range	V_{ICMP}			0		V_{DD}	V
Internal reference voltage deviation	ΔV_{IREF}	CmRVM register value: 7FH to 80H (m = 0, 1)				±2	LSB
		Other than above				±1	LSB
Response time	t_{CR}, t_{CF}	Input amplitude = ±100 mV			70	150	ns
Operation stabilization time Note 1	t_{CMP}	CMPnEN = 0→1	V_{DD} = 3.3 to 5.5 V			1	μs
			V_{DD} = 2.7 to 3.3 V			3	
Reference voltage stabilization wait time	t_{VR}	CVRE: 0→1 Note 2				20	μs

Note 1. Time required after the operation enable signal of the comparator has been changed (CMPnEN = 0 → 1) until a state satisfying the DC and AC characteristics of the comparator is entered.

Note 2. Enable operation of internal reference voltage generation (CVREm bit = 1; m = 0, 1) and wait for the operation stabilization wait time before enabling the comparator output (CnOE bit = 1; n = 0, 1).



2.7.4 Programmable gain amplifier

(T_A = -40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	V_{IOPGA}				±5	±10	mV
Input voltage range	V_{IPGA}			0		0.9 × V_{DD}/gain	V
Response time	V_{OHPGA}			0.9 × V_{DD}			V
	V_{OLPGA}					0.1 × V_{DD}	
Gain error	—	4, 8 times				±1	%
		16 times				±1.5	
		32 times				±2	
Slew rate	SR_{RPGA}	Rising edge	4.0 V ≤ V_{DD} ≤ 5.5 V	1.4			V/μs
			2.7 V ≤ V_{DD} ≤ 4.0 V	0.5			
	SR_{FPGA}	Falling edge	4.0 V ≤ V_{DD} ≤ 5.5 V	1.4			
			2.7 V ≤ V_{DD} ≤ 4.0 V	0.5			
Operation stabilization wait time Note	t_{PGA}	4, 8 times				5	μs
		16, 32 times				10	

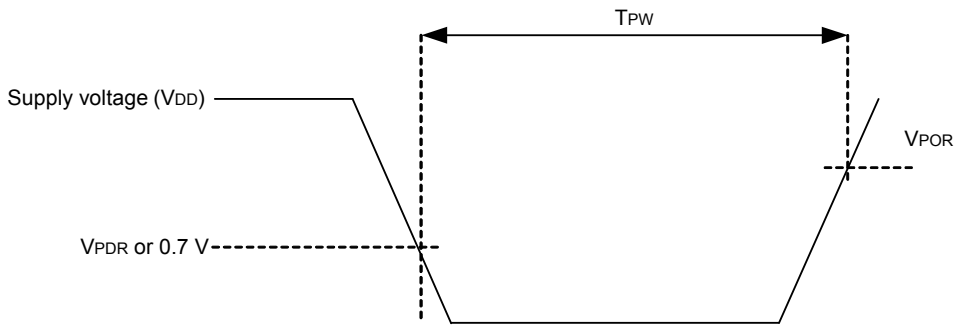
Note Time required after the PGA operation has been enabled (PGAEN = 1) until a state satisfying the DC and AC specifications of the PGA is entered.

2.7.5 POR circuit characteristics

(T_A = -40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.47	1.51	1.55	V
	V_{PDR}	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width Note	t_{PW}		300			μs

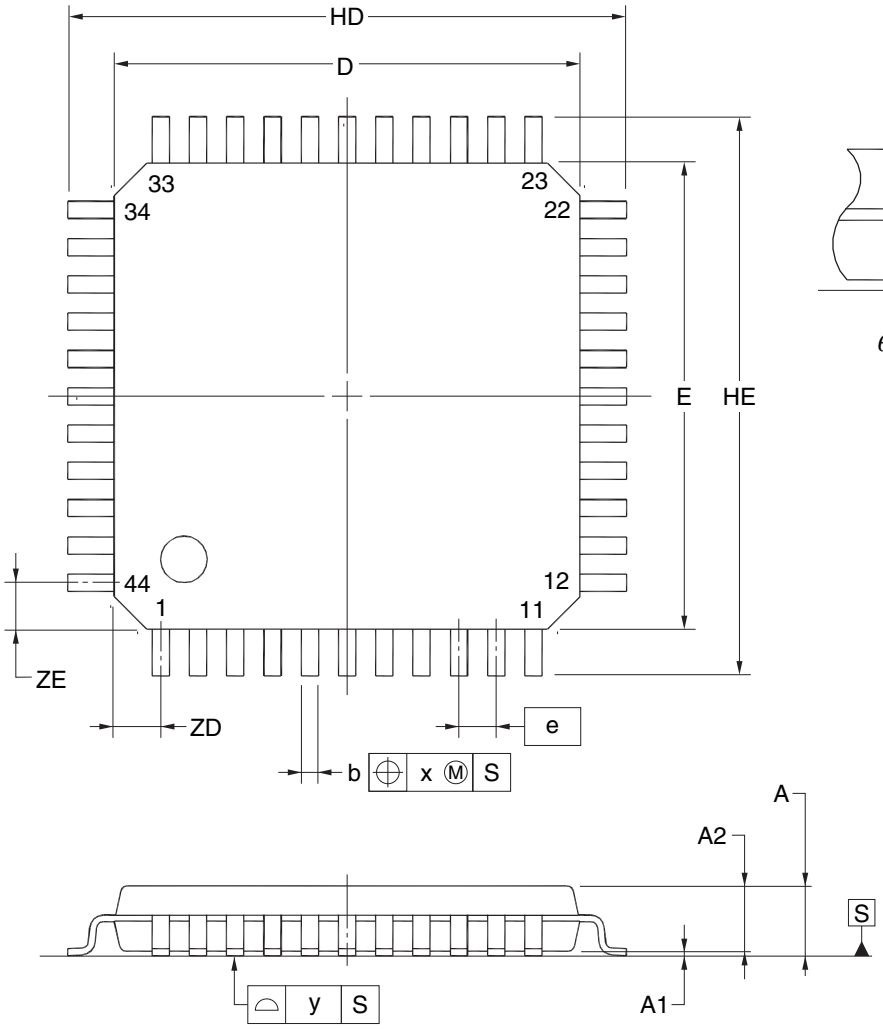
Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



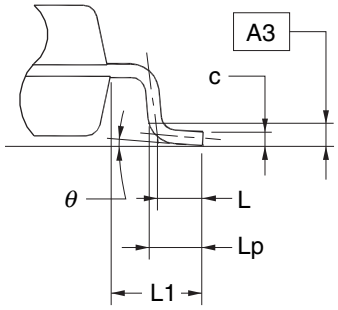
3.3 44-pin Products

R5F11EF8AFP, R5F11EFAAFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	10.00±0.20
E	10.00±0.20
HD	12.00±0.20
HE	12.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	$0.37^{+0.08}_{-0.07}$
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
e	0.80
x	0.20
y	0.10
ZD	1.00
ZE	1.00

NOTE
Each lead centerline is located within 0.20 mm of its true position at maximum material condition.

REVISION HISTORY	RL78/G1G Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Jul 31, 2014	—	First Edition issued
1.20	Mar 25, 2015	1	Change of description in 1.1 Features
		3	Change of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1G
		3	Change of Table 1 - 1 Orderable Part Numbers
		11	Change of 1.6 Outline of Functions
1.30	Sep 30, 2016	1	Addition of Note to 1.1 Features
		4	Modification of Pin configuration in 1.3.1 30-pin products
		5	Modification of Pin configuration in 1.3.2 32-pin products
		6	Modification of Pin configuration in 1.3.3 44-pin products
		63	Change of Note in 2.8 RAM Data Retention Characteristics

Caution: This product uses SuperFlash® technology licensed from Silicon Storage Technology, Inc.

NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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